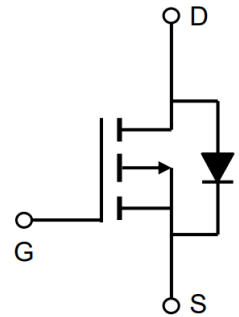


-60V P-Channel Enhancement Mode MOSFET

Description

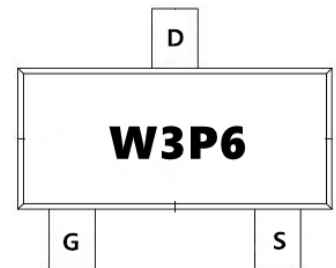
The AP3P06MI uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



General Features

$V_{DS} = -60V$ $I_D = -3.8A$

$R_{DS(ON)} < -150m\Omega$ @ $V_{GS} = -10V$ (Type: 125m Ω)



Application

- Battery protection
- Load switch
- Uninterruptible power supply



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP3P06MI	SOT23-3L	W3P6	3000

Absolute Maximum Ratings ($T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-3.8	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-2.4	A
I_{DM}	Pulsed Drain Current ²	-12	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation ³	1.5	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	125	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	80	$^\circ C/W$

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Electrical Characteristics ($T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-60	-67	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=-1\text{mA}$	---	-0.021	---	V/ $^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10V, I_D=-1.5A$	---	125	150	m Ω
		$V_{GS}=-4.5V, I_D=-1A$	---	158	200	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.0	1.7	-2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.08	---	mV/ $^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-48V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	uA
		$V_{DS}=-48V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-5V, I_D=-1.5A$	---	5.9	---	S
Q_g	Total Gate Charge (-4.5V)	$V_{DS}=-20V, V_{GS}=-4.5V, I_D=-1.5A$	---	4.6	---	nC
Q_{gs}	Gate-Source Charge		---	1.4	---	
Q_{gd}	Gate-Drain Charge		---	1.62	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DS}=-15V, V_{GS}=-10V, R_G=3.3\Omega, I_D=-1A$	---	17.4	---	ns
T_r	Rise Time		---	5.4	---	
$T_{d(off)}$	Turn-Off Delay Time		---	37.2	---	
T_f	Fall Time		---	2.4	---	
C_{iss}	Input Capacitance	$V_{DS}=-15V, V_{GS}=0V, f=1\text{MHz}$	---	531	---	pF
C_{oss}	Output Capacitance		---	59	---	
C_{rss}	Reverse Transfer Capacitance		---	38	---	
I_S	Continuous Source Current ^{1,4}	$V_G=V_D=0V$, Force Current	---	---	-1.7	A
I_{SM}	Pulsed Source Current ^{2,4}		---	---	-7	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=-1A, T_J=25^\circ\text{C}$	---	---	-1.2	V

Note :

- 1、The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3、The power dissipation is limited by 150°C junction temperature
- 4、The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

-60V P-Channel Enhancement Mode MOSFET

P-Channel Typical Characteristics

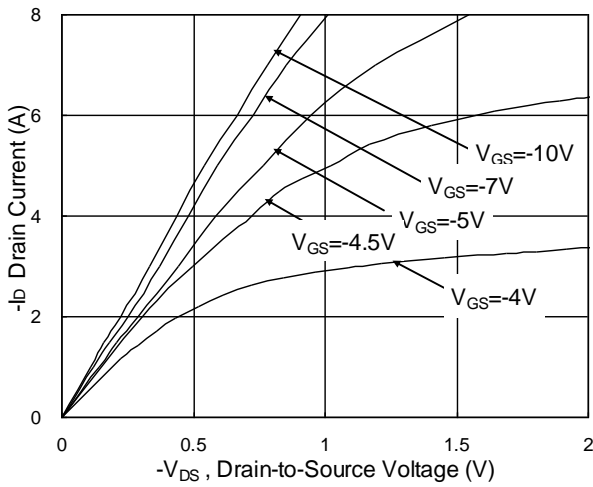


Fig.1 Typical Output Characteristics

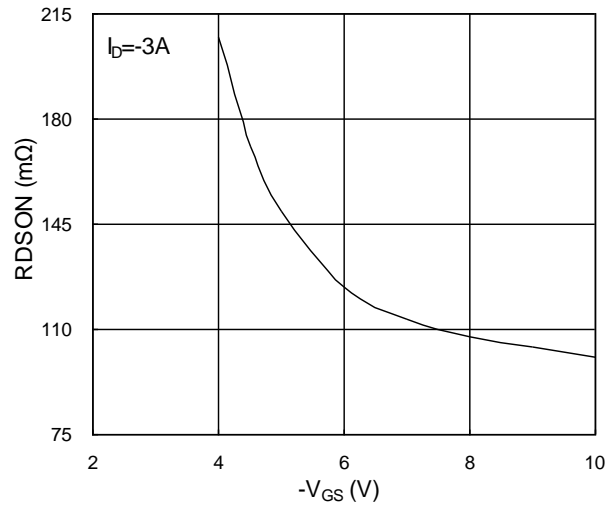


Fig.2 On-Resistance vs. G-S Voltage

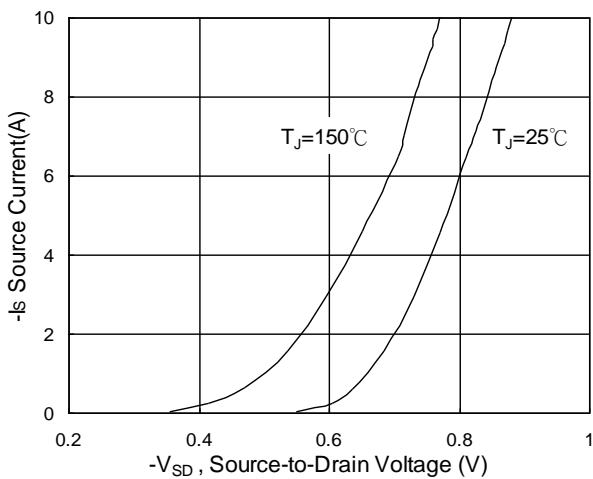


Fig.3 Forward Characteristics Of Reverse

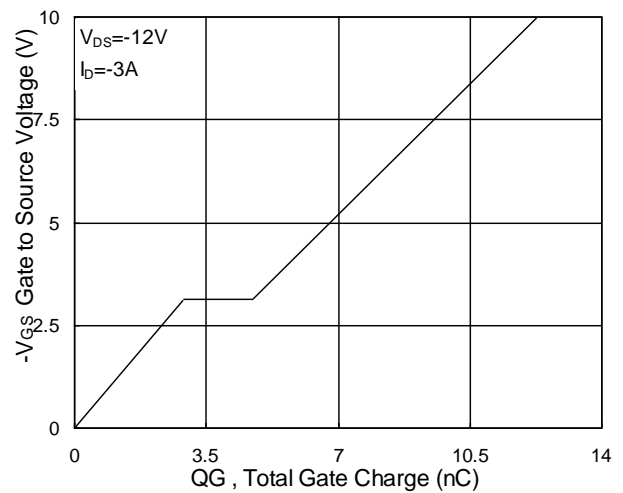


Fig.4 Gate-Charge Characteristics

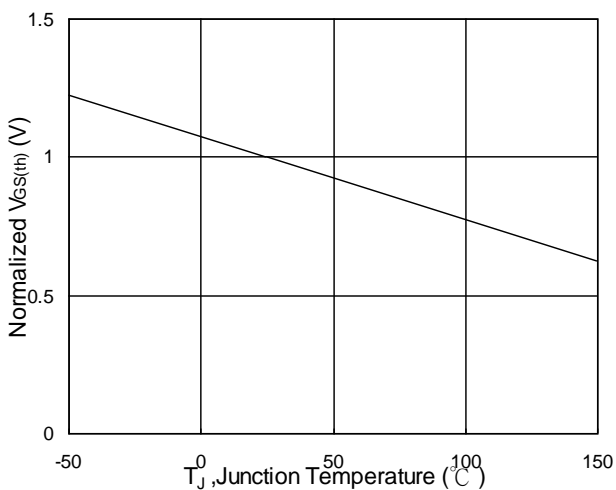


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

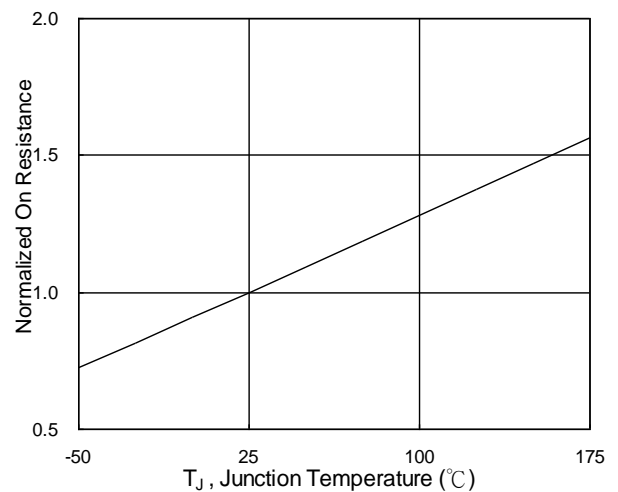


Fig.6 Normalized $R_{DS(on)}$ vs. T_J



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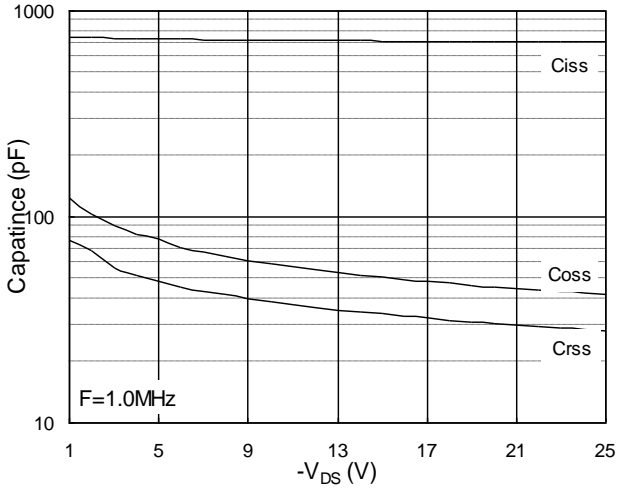


Fig.7 Capacitance

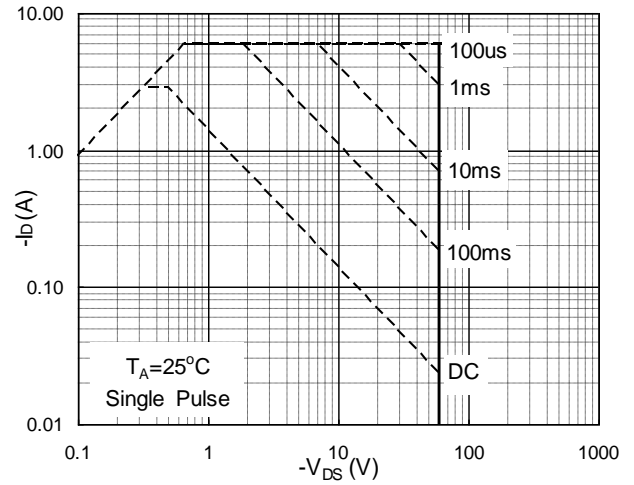


Fig.8 Safe Operating Area

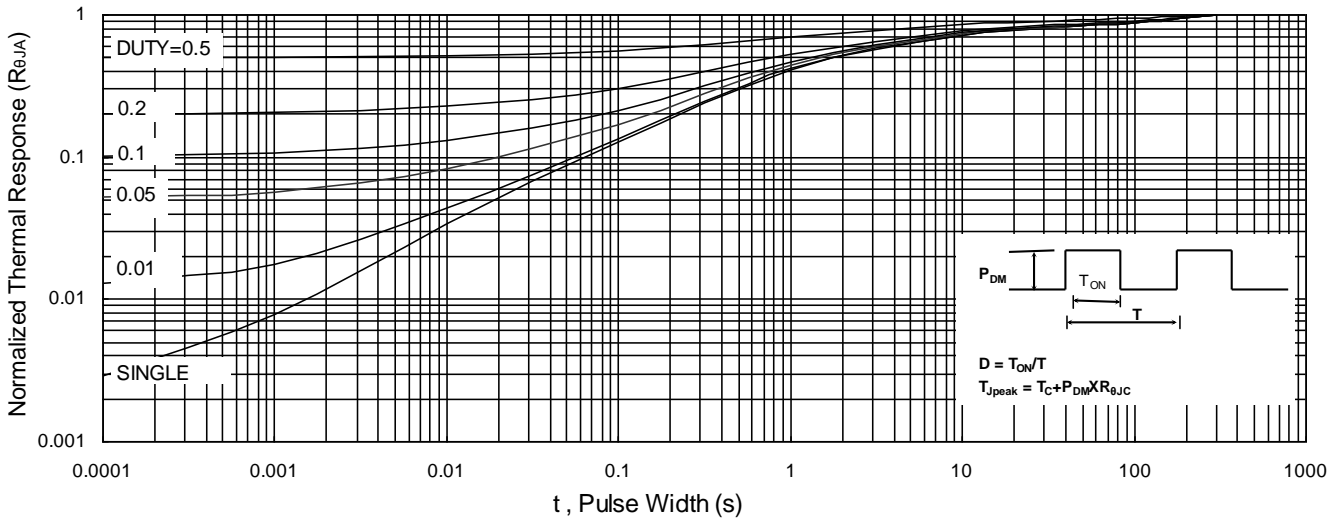


Fig.9 Normalized Maximum Transient Thermal Impedance

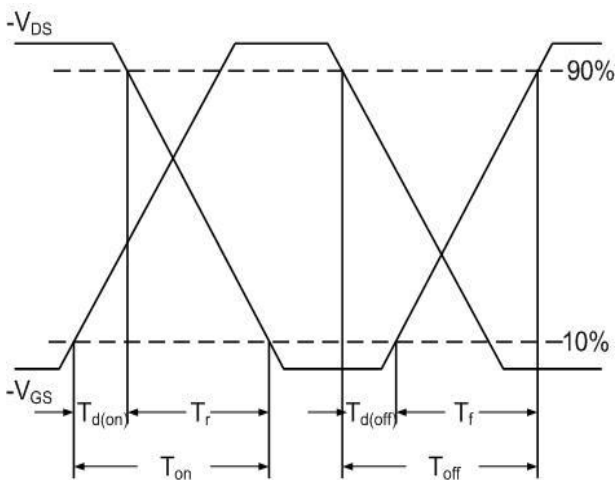


Fig.10 Switching Time Waveform

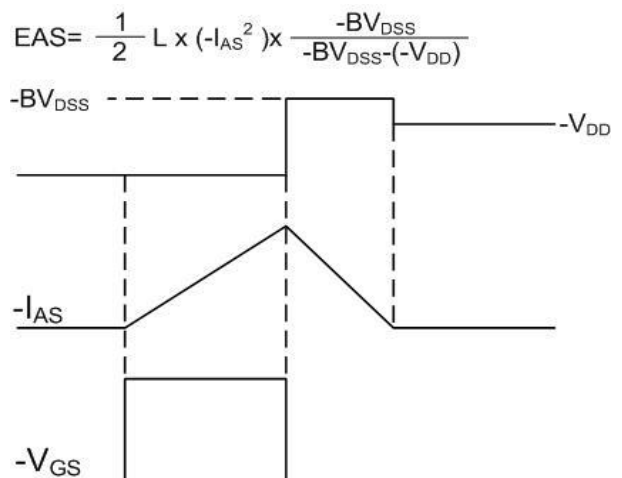
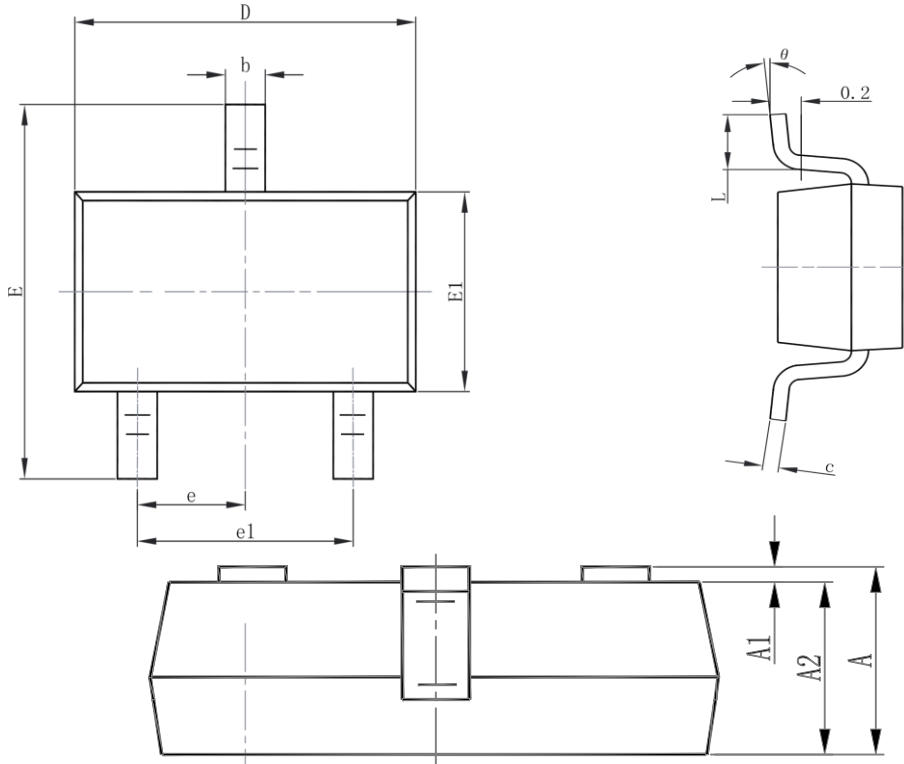


Fig.11 Unclamped Inductive Waveform

Package Mechanical Data-SOT23-3



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

-60V P-Channel Enhancement Mode MOSFET**Attention**

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Edition	Date	Change
RVE1.0	2021/3/1	Initial release

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